Vishay Semiconductors

Thyristor Surface Mount, Phase Control SCR, 8 A



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PRIMARY CHARACTERISTICS				
I _{T(AV)}	8 A			
V _{DRM} /V _{RRM}	800 V			
V _{TM}	1.2 V			
I _{GT}	15 mA			
TJ	-40 to +125 °C			
Package	D ² PAK (TO-263AB)			
Circuit configuration	Single SCR			

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47

RoHS COMPLIANT HALOGEN

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · Input rectification and crow-bar (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-12TTS08S-M3 High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS					
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А		

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	8				
I _{T(RMS)}		12.5	A			
V _{RRM} /V _{DRM}		800	V			
I _{TSM}		110	A			
V _T	8 A, T _J = 25 °C	1.2	V			
dV/dt		150	V/µs			
dl/dt		100	A/µs			
TJ	Range	-40 to +125	°C			

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 ℃ mA				
VS-12TTS08S-M3	800	800	1.0				

VS-12TTS08S-M3 Series



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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum average on-state current	I _{T(AV)}		8				
Maximum RMS on-state current	I _{T(RMS)}	$T_{C} = 108 \ ^{\circ}C$, 180° conduction, half sine wave	12.5	^			
Maximum peak one-cycle		10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	95	A			
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, T_J = 125 °C	110				
Marian and 124 for final and	l ² t	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s			
Maximum I ² t for fusing	141	10 ms sine pulse, no voltage reapplied, $T_J = 125 \text{ °C}$	64				
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, T_J = 125 °C	640	A²√s			
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V			
On-state slope resistance	r _t	T _{.1} = 125 °C	16.2	mΩ			
Threshold voltage	V _{T(TO)}	IJ = 125 C	0.87	V			
Maximum reverse and direct lookage surrent	I _{RM} /I _{DM}	$T_J = 25 ^{\circ}C$	0.05				
Maximum reverse and direct leakage current		$T_J = 125 \text{ °C}$ $V_R = \text{Rated } V_{RRM} / V_{DRM}$	1.0				
Typical holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	30	mA			
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	50				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = Open$	150	V/µs			
Maximum rate of rise of turned-on current	dl/dt	· · · · · · · · · · · · · · · · · · ·	100	A/µs			

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	vv		
Maximum peak positive gate current	+ I _{GM}		1.5	А		
Maximum peak negative gate voltage	- V _{GM}		10	V		
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	20			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	15	mA		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	10			
		Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	1.2			
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	1	V		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	0.7	v		
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V Detectivelye	0.2			
Maximum DC gate current not to trigger	I _{GD}	$T_J = 125 \text{ °C}, V_{DRM} = \text{Rated value}$		mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8			
Typical reverse recovery time	t _{rr}	Т, ₁ = 125 °С	3	μs		
Typical turn-off time	t _q	1] = 125 0	100			

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS
Maximum junction and st temperature range	orage	T _J , T _{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case RthJ		R _{thJC}	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance case to heatsink	е,	R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque -	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking device			Case style D ² PAK (TO-263AB)	12TT	S08S

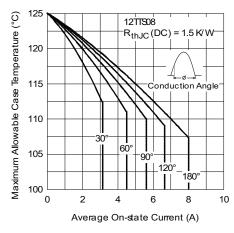


Fig. 1 - Current Rating Characteristics

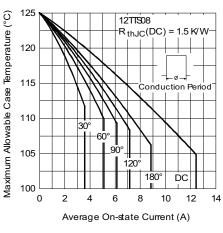


Fig. 2 - Current Rating Characteristics

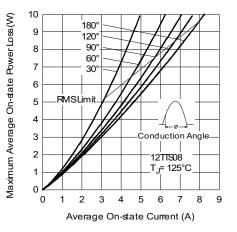
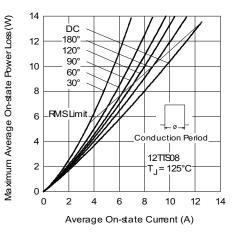
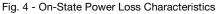


Fig. 3 - On-State Power Loss Characteristics





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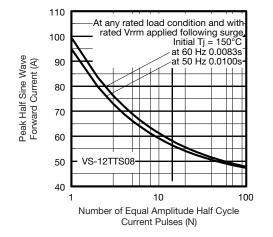


Fig. 5 - Maximum Non-Repetitive Surge Current

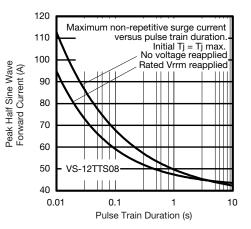


Fig. 6 - Maximum Non-Repetitive Surge Current

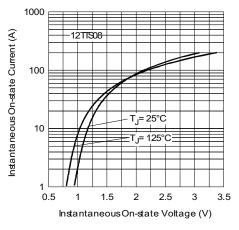
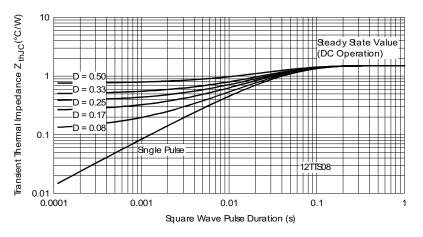
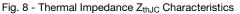


Fig. 7 - On-State Voltage Drop Characteristics





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ORDERING INFORMATION TABLE

Device code	vs-	12	т	т	s	08	s	TRL	-M3
	1	2	3	4	5	6	7	8	9
	1	- Visl	hay Sen	nicondu	ctors pro	oduct			
	2	- Cur	rent rati	ng (12.5	5 A)				
	3	- Circ	cuit conf	iguratior	า:				
		T =	single t	hyristor					
	4	- Pac	kage:						
		T =	D ² PAK	(TO-263	BAB)				
	5	- Тур	e of silio	con:					
		S =	standa	rd recov	ery rect	ifier			
	6	- Volt	tage rati	ing (08 =	= 800 V))			
	7.	- S =	surface	mounta	ble				
	8	• No	one = tu	be					
		• TF	RL = tap	e and re	el (left o	oriented	l)		
		• TF	RR = tap	be and r	eel (righ	t orient	ed)		
	9	-M3	= halog	gen-free	, RoHS-	complia	ant, and	termina	ations le

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-12TTS08S-M3	50	Antistatic plastic tubes				
VS-12TTS08STRL-M3	800	13" diameter plastic tape and reel				
VS-12TTS08STRR-M3	800	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96164			
Part marking information	www.vishay.com/doc?95444			
Packaging information	www.vishay.com/doc?96424			



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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIMETERS		INCHES		NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

S١	SYMBOL	MILLIMETERS		INCHES		NOTES
	STWBUL	MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54 BSC		0.100 BSC		
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25 BSC		0.010 BSC		
	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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